



# PRODUCT DATA SHEET



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Datasheet

ces Sami

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.

**ESD Protection Diode Array** 

#### **Features**

- 150Watts peak pulse power (tp =  $8/20\mu$ s)
- SOT23-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.3pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 ±12kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20μs)



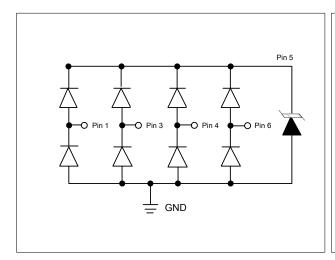
## **Applications**

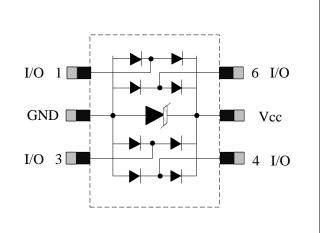
- Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

### **Mechanical Data**

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## **Schematic & PIN Configuration**







**Absolute Maximum Rating** 

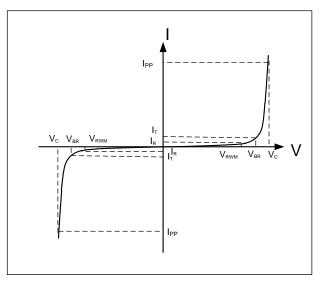
Rating	Symbol	Value	Units
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	150	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	$I_{pp}$	5.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{\mathrm{ESD}}$	15 12	kV
Lead Soldering Temperature	$T_{L}$	260(10seconds)	$^{\circ}\mathbb{C}$
Junction Temperature	$T_{J}$	-55 to + 125	°C
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$ C

## **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25℃			1.0	uA
Peak Pulse Current	$I_{PP}$	tp =8/20μs			5.0	A
Clamping Voltage	$V_{\rm C}$	$I_{PP}=5.0A, t_p=8/20\mu s$			16	V
Junction Capacitance	$C_{j}$	$V_R = 0V$ , $f = 1MHz$ IO to IO		0.3	0.45	pF
		$V_R = 0V$ , $f = 1MHz$ IO to GND		0.6	0.9	

# Electrical Parameters (TA = $25 \, ^{\circ}$ C unless otherwise noted)

Symbol	Parameter		
$\mathbf{I}_{ ext{PP}}$	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
V <sub>RWM</sub>	Working Peak Reverse Voltage		
Ir	Maximum Reverse Leakage Current @ VRWM		
$V_{\text{BR}}$	Breakdown Voltage @ IT		
IT	Test Current		



Note:.  $8/20\mu s$  pulse waveform.



## **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

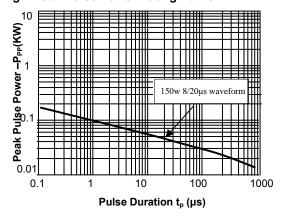


Fig.3 Pulse Waveform-8/20µs

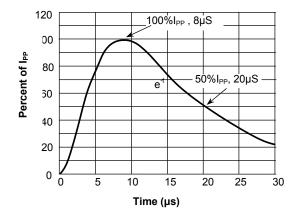


Fig.2 Pulse Derating Curve

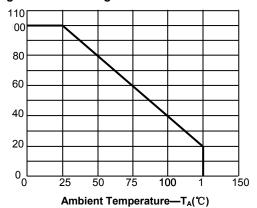
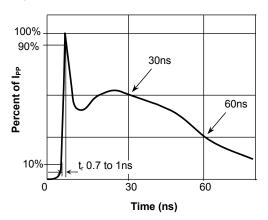
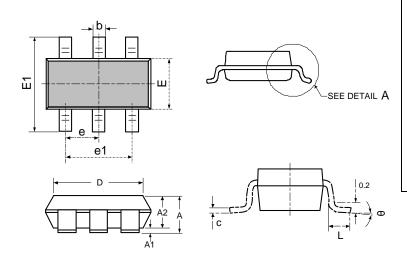


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)



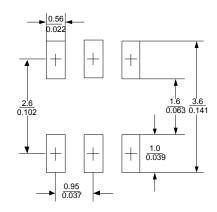


# $Outline\ Drawing-SOT 23-6$ PACKAGE OUTLINE



DIMENSIONS						
SYMBOL	INCHES		MILLIMETER			
	MIN	MAX	MIN	MAX		
Α	0.041	0.049	1.050	1.250		
A1	0.000	0.004	0.000	0.100		
A2	0.041	0.045	1.050	1.150		
D	0.111	0.119	2.820	3.020		
E	0.059	0.067	1.500	1.700		
E1	0.104	0.116	2.650	2.950		
b	0.012	0.020	0.300	0.500		
е	0.037(BSC)		0.950(BSC)			
e1	0.071	0.079	1.800	2.000		
L	0.012	0.024	0.300	0.600		
θ	0°	8°	0°	8°		





Notes

1. This land pattern is for reference purposes only consult your manufacturing group to ensure your company's manufacturing guidelines are met.



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